

**MOSFETs Silicon 100V N-Channel MOS****■ Applications**

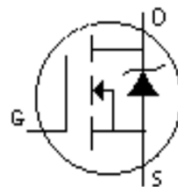
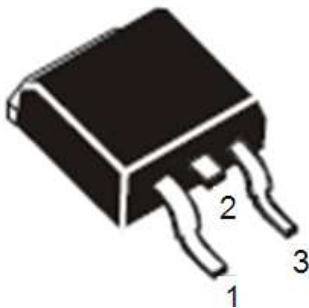
- Synchronus Rectification
- Industrial and Motor Drive
- DC/DC and AC/DC Converters
- Power Tools

■ Features

- High-Speed Switching
- Low $R_{DS(ON)}$
- Low Gate Charge
- Enhanced Avalanche Ruggedness
- RoHS and Halogen-Free Compliant
- 100% UIS and RG Tested

■ Product Summary

V_{DS}	100	V
I_D	70	A
$R_{DS(ON)}, T_{yp}@10V$	15	m Ω
Q_g	150	nC



Gate: 1
Drain: 2
Source: 3

TO-263

Marking	Package	Packaging	Min. package quantity
ML020R100PH	TO-263	Tube	1000
ML020R100PH	TO-263	Tape & Reel	800





■ Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current Tc=25°C (Note 1)	I_D	70	A
Continuous Drain Current Tc=100°C (Note 1)		45	A
Drain Current-Pulsed (Note 1)	I_{DM}	190	A
Total Dissipation	P_D	227	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C
Single Pulse Avalanche Energy (Note 2)	E_{AS}	1050	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

■ Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	0.55	°C/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	60	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD}=100V$, $T_{ch}=25^\circ C$ (initial), $L=0.5mH$, $R_g=25\Omega$.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



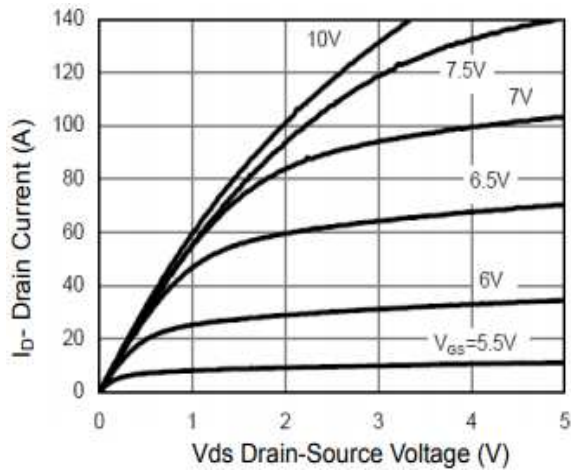
■ Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
Static Parameters							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA		200	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =200V, V _{GS} =0V		-	-	1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V		-	-	±100	nA
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA		2	3	4	V
Drain-Source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A		-	15	20	mΩ
			Tj=125℃	-	31	-	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{DS} =35V, V _{GS} =0V, f=1.0MHz		-	2750	-	pF
Output Capacitance	C _{oss}			-	485	-	pF
Reverse Transfer Capacitance	C _{rss}			-	180	-	pF
Gate Resistance	R _g	V _{DS} =0V, V _{GS} =0V, f=1.0MHz		-	0.8	-	Ω
Switching Paramters							
Turn-On Delay Time	t _{d(on)}	V _{DS} =100V, I _D =20A, V _{GS} =10V, R _G =10Ω		-	18	-	ns
Turn-On Rise Time	t _r			-	67	-	ns
Turn-Off Delay Time	t _{d(off)}			-	60	-	ns
Turn-Off Fall Time	t _f			-	55	-	ns
Total Gate Charge	Q _g	V _{DS} =100V, I _D =20A, V _{GS} =10V		-	150	-	nC
Gate-Source Charge	Q _{gs}			-	33	-	nC
Gate-Drain Charge	Q _{gd}			-	30	-	nC
Source-Drain Characteristics							
Diode Forward Voltage	V _{sd}	V _{GS} =0V, I _S =10A		-	0.8	1.2	V
Reverse Recovery Time	t _{rr}	V _R =100V, I _F =20A, di/dt=100A/us		-	180	-	ns
Reverse Recovery Charge	Q _{rr}			-	1.2	-	uC

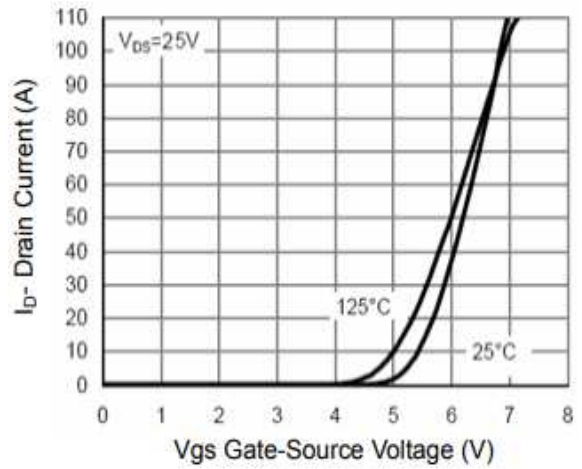




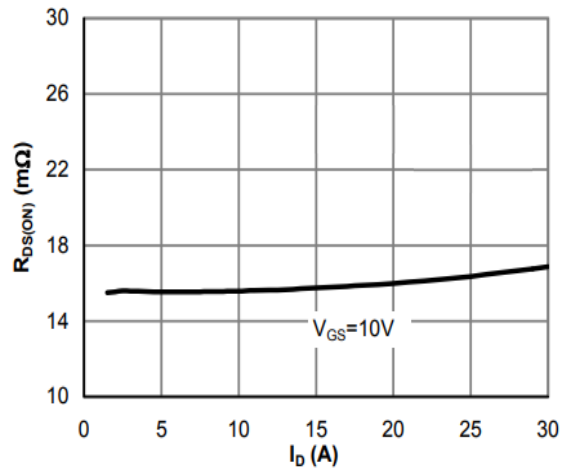
■ Characteristics Curves



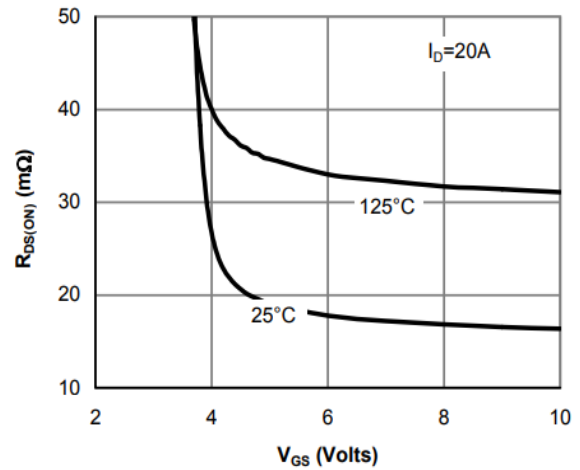
Output Characteristics



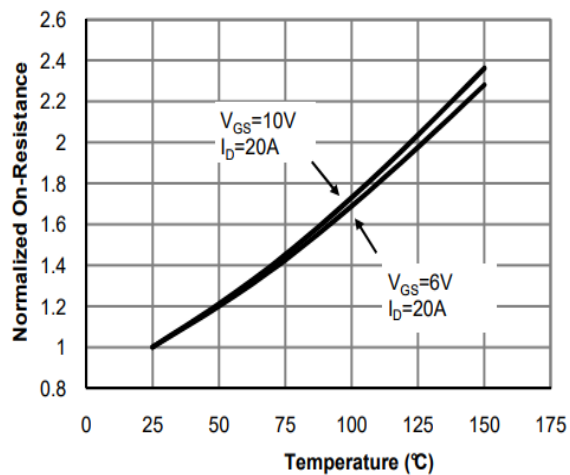
Transfer Characteristics



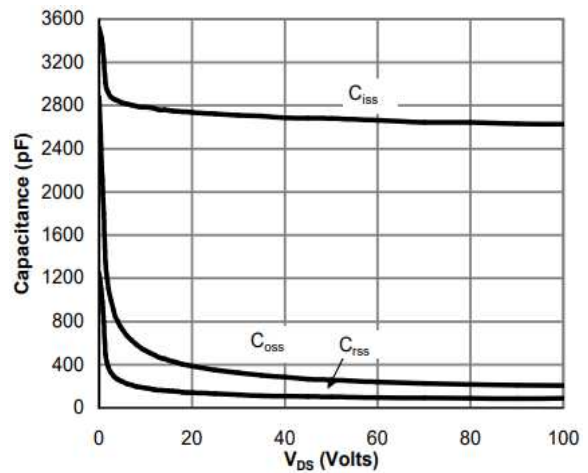
On Resistance Vs Drain Current



On Resistance Vs Gate Source Voltage

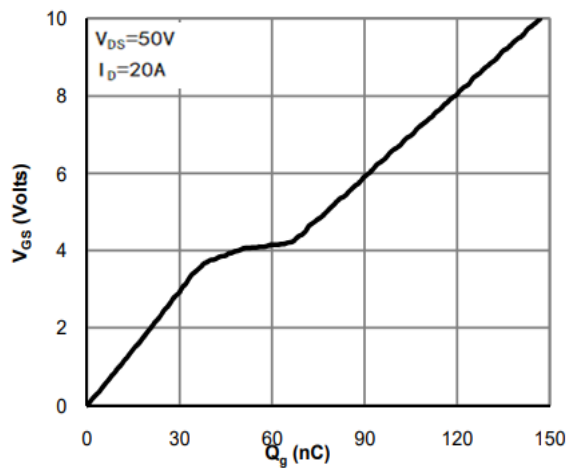


Rdson-JunctionTemperature

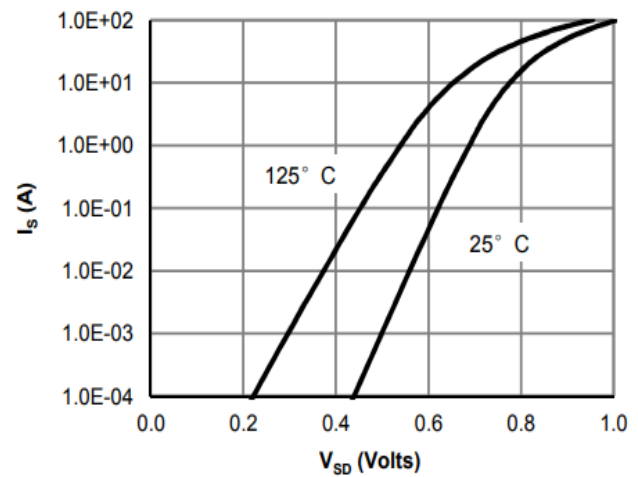


Capacitance

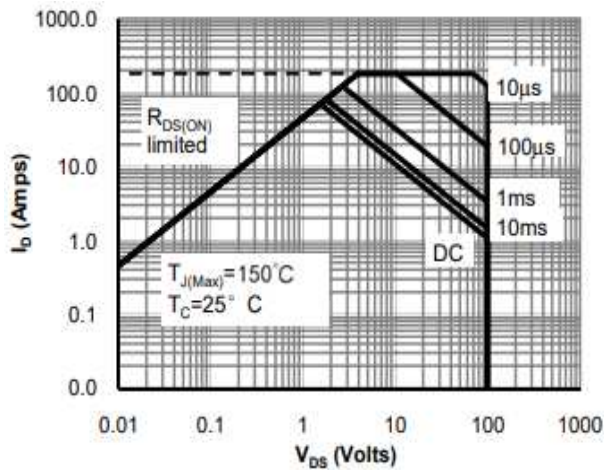




Gate Charge Waveform



Source-Drain Diode Forward Voltage



Maximum Safe Operating Area

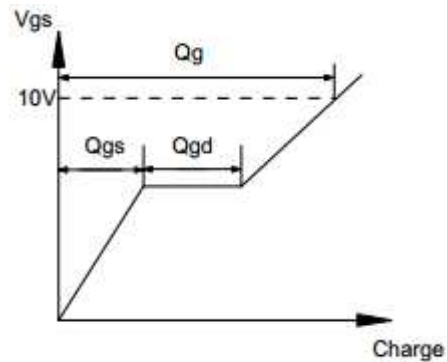
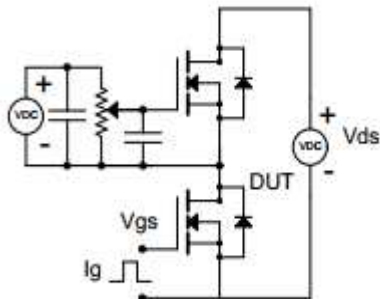
Note : The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



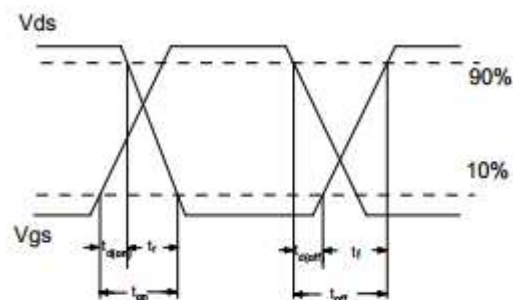
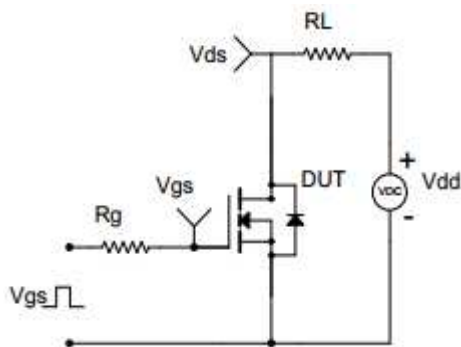


■ Test Circuit & Waveform

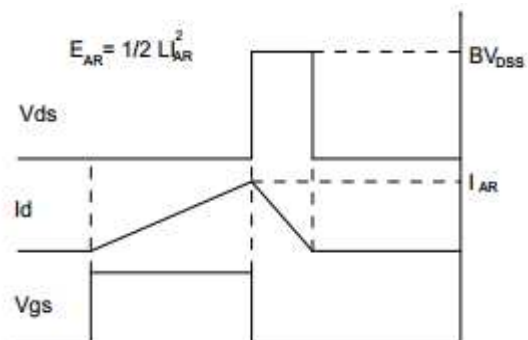
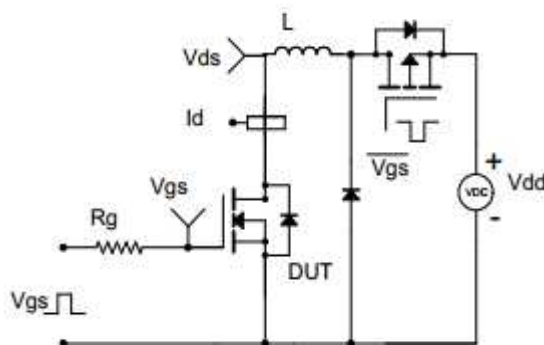
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform





■ TO-263 Package Dimensions

Unit: mm

Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	4.42		4.72	e1	2.44	2.54	2.64
B	1.22		1.4	e2	4.98		5.18
b	0.76		0.86	L1	14.7	15.1	15.5
b1	1.22		1.4	L2	2	2.3	2.6
b2	0.33		0.43	L3	1.5		2
C	1.22		1.35	K	-0.1		0.1
D	9.95		10.25	Y	8.51	8.61	8.71
E	8.99		9.29				

